

Application No.: 10/667,229

Docket No.: JCLA10892

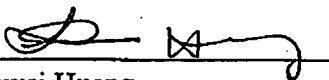
REMARKS**Present Status of the Application**

Applicants appreciate that claims 1-19 have been allowed.

Applicants have amended claim 5, in which the statement "wherein the annealing temperature in the pre-annealing operation is lower than the operating temperature in the solid phase epitaxial process" at lines 14-16 is canceled since the method of manufacturing a MOS transistor as defined in claim 5 does not refer to comprising a step of the pre-annealing operation. It is believed that this amendment does not change the consideration of patentability and should be acceptable.

For foregoing reasons, entry of the amendment is requested.

Respectfully submitted,
J.C. PATENTS

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